

MRF6V14300HSR5 :Part Detail

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General Information

Part Number	MRF6V14300HSR5
Description	Pulse Lateral N-Channel RF Power MOSFET, 1400 MHz, 330 W, 50 V
Product Line	614300HS
PTI	RGDL
Material Type	Tested Packaged Device
Life Cycle Description (code)	PRODUCT MATURITY/SATURATION
Status	Active
Application/Qualification Tier	10-YEARS APPLICATION LIFE

Package Information

Package Type and Termination Count	Air Cavity 3
Package Description and Mechanical Drawing	NI-780S
Device Weight(g)	3.27290
Package Length (nominal)(mm)	0.810
Package Width (nominal)(mm)	0.390
Package Thickness (nominal)(mm)	3.760
Tape & Reel	Yes

Environmental and Compliance Information

Pb-Free	
RoHS Compliant	
Halogen Free	Yes
Material Composition Declaration (MCD)	Download MCD Report Download MCD Report
RoHS Certificate of Analysis (CoA)	Download RoHS CoA Report
2nd Level Interconnect	e4
Peak Package Body Temperature (PPT)(°C)	260
Downloaded from Arrow.com	TV

Temperature (s)	
Number of Reflow Cycles	3
REACH SVHC	NXP REACH Statement

Manufacturing Information

Micron Size(μm)	6
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Ordering Information

Minimum Package Quantity (MPQ)	50
MPQ Container	REEL
Exempt from Minimum Delivery Value	Yes
Preferred Order Quantity (POQ)	50
POQ Container	BOX
Export Control Classification Number (US)	EAR99
Harmonized Tariff (	
CCATS Document	-
ENC Status	-
Other Trade Compliance Documents	-
Budgetary Price excluding tax(US Currency)	-
Order	

Product/Process Change Notice (PCN)

Number	Type	Title	Issue Date	Effectivity Date
13811	Product Change Notice	Reduction in Gold Plating Thickness for RF Power Transistor Products	15 Dec 2009	01 Apr 2010
13952	Product Change Notice	RF Power Transistor Internal Matching Capacitor Wafer Fab Transfer	15 Dec 2009	15 Mar 2010
13618	Product Change Notice	RF High Power LDMOS - Additional Assembly and Test Site	28 May 2009	26 Aug 2009
13328	Product Change Notice	Planned LDMOS Fab Transfer	12 Nov 2008	10 Feb 2009

Operating Characteristics

Class	AB
Die Technology	LDMOS
Efficiency (Typ) (%)	60.5
Frequency (Min) (MHz)	1200
Frequency Band (Min-Max) (MHz)	1200 to 1400
Frequency Max (Max) (MHz)	1400

Matching	I/O
Output Power (Typ) (W) @ Intermodulation Level at Test Signal	330 @ Peak
P1dB (Typ) (dBm)	55.2
P1dB (Typ) (W)	330
P3dB (Typ) (W)	339
Power Gain (Typ) (dB) @ f (MHz)	18 @ 1400
Sample Exception Availability	N
Supply Voltage (Typ) (V)	50
Test Signal	Pulse
Thermal Resistance (Spec)	0.13

Suggested Drivers



Reliability Data Lookup

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